

Radioactivity

① $A = -\frac{dN}{dt} = \lambda N$
 disintegrating nuclei = λN
 remained nuclei = N

② N_0 = initial nuclei
 N = remained nuclei.
 n = no. of half life.

③ NO. of nuclei after n half life.

$$N = \frac{N_0}{2^n} \quad n = \frac{\text{given}}{t/2}$$

$$t/2 = \frac{0.693}{\lambda} \quad \text{or} \quad \frac{2.3 \log 2}{\lambda} = \frac{\ln 2}{\lambda}$$

④ Probability of decay.

$$1 - \left(\frac{1}{2}\right)^n$$

Probability of survival of life

$$\frac{1}{2^n} \text{ of } \frac{N_0}{N_0}$$

⑤ Mean or Average life (τ)

$$\tau = \frac{1}{\lambda} = 1.44 t/2$$

$$N = N_0 e^{-\lambda t}$$

$$t = \frac{2.3 \log \frac{N_0}{N}}{\lambda}$$

$$t_2 - t_1 = \frac{2.3 \log \frac{N_1}{N_2}}{\lambda}$$

$$t/2 = \frac{0.693}{\lambda} = \frac{2.3 \log 2}{\lambda}$$

λ = power, I = Intensity

photoelectric effect & Dual Nature

① photoelectric efficiency

$$\eta = \frac{\text{no. of photoe}^\ominus \text{ emitted}}{\text{no. of photons incidented}}$$

② Einstein's photoelectric eqⁿ

$$K_{\max} = E - W = h\nu - h\nu_0$$

$$K_{\max} = \frac{hc}{\lambda} - \frac{hc}{\lambda_0}$$

⇒ photoelectric emission takes place

Instantaneously 10^{-10} sec

$$hc = 12400 \text{ eV-}\overset{\text{Å}}{\text{Å}} = 20 \times 10^{-26} \text{ J-m}$$

$$hc = 1240 \text{ eV-nm}$$

⇒ If energy of light radⁿ becomes (n) times, then max. K.E of emitted photoe[⊖] becomes greater than (n) times.

③ $eV_0 = K - W$
 $V_0 = \frac{h\nu}{e} - \frac{W}{e}$

④ photon theory

a) No. of photons = $\frac{E}{h\nu}$

b) NO of photons / time (N/t) = $\frac{\text{Power}}{h\nu}$

c) No. of photons / time / Area. = $\frac{\text{Intensity}}{h\nu}$

⑤ momentum (p) = $\frac{E}{c} = \frac{h}{\lambda}$ - for photons.

| Surface | AP | (F) | Radiation pressure |
|---|---------------------------------------|--------------------------------|-------------------------------|
| i) Perfectly reflecting | $\Delta p = \frac{2E}{c}$ | $F = \frac{2W}{c}$ | $P = \frac{2I}{c}$ |
| ii) Perfectly Absorbing | $\Delta p = \frac{E}{c}$ | $F = \frac{W}{c}$ | $P = \frac{I}{c}$ |
| iii) partially reflecting having Reflecting coefficient | $\Delta p = \frac{E}{c}(1+r)$ | $F = \frac{W}{c}(1+r)$ | $P = \frac{I}{c}(1+r)$ |
| iv) angle | $\Delta p = \frac{2E}{c}(\cos\theta)$ | $F = \frac{2W}{c}(\cos\theta)$ | $P = \frac{2I}{c} \cos\theta$ |

$$2\sqrt{2} = 2.8$$

De-Broglie wavelength

$$\lambda = \frac{h}{p} = \frac{hc}{E} \quad (\text{for only photons})$$

$$\lambda = \frac{h}{mv} = \frac{h}{\sqrt{2m \cdot k}} = \frac{h}{\sqrt{2m \cdot eV_{acc}}} \quad (\text{for matter})$$

$$\lambda = \frac{h}{2\pi \hbar}$$

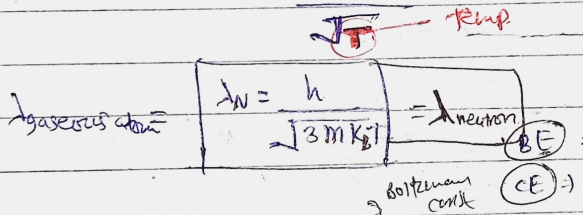
a) electron: $\lambda_{e^-} = \frac{12.27}{\sqrt{V}} \text{ \AA}$

b) proton: $\lambda_p = \frac{0.128}{\sqrt{V}} \text{ \AA} \Rightarrow \frac{0.252}{\sqrt{V}} \text{ \AA}$

c) Deuteron: $\lambda_D = \frac{0.1}{\sqrt{V}} \text{ \AA}$

d) α -particle: $\lambda_{\alpha} = \frac{0.1}{\sqrt{V}} \text{ \AA}$

e) Neutron: $\lambda_N = 90.83$



Kinetic energy: $\frac{3}{2} k_B T$ (gaseous atom)

(i) $\beta = \frac{I_C}{I_B}$ (β -current gain)

(ii) Voltage gain = $\frac{V_C}{V_B} = \beta_{RC} \times \text{Resistance gain}$

(iii) Resistance gain = R_C / R_B

(iv) Power gain: $\beta \times \text{Voltage gain} = \frac{(V_{gain})^2}{R_{gain}} \Rightarrow \beta^2 \times R_{gain}$

$$\frac{1}{\alpha} = \frac{1}{\beta} + 1$$

α = current gain for CB configuration

current amplification factor $\Rightarrow \beta$ = current gain for CE configuration

Universal gate

$$XOR \Rightarrow \bar{A} \cdot B + A \cdot \bar{B}$$

$$\frac{E}{s} = \frac{I}{A}$$

Semiconductors

$$(w+x)(w+y) \neq w+(x \cdot y)$$

(Ge) (Si)

0.7

1.1

(Eg) Energy gap

0.3V

0.7V

(V_B) Potential barrier

$\sim 10^{19}/m^3$ $\sim 10^{16}/m^3$ e^- density

$$n_e \times n_h = n_i^2$$

$$i = n_e A V_e + n_h A V_h \quad \sigma = n_e v_e + n_h v_h$$

(i) mobility of e^-

$$\mu = \frac{|V_d|}{E}$$

$$\sigma = e(n_e \mu_e + n_h \mu_h)$$

(1) Forward biasing

$$V_{net} = V_{ext} - V_{barrier/di}$$

(2) Reverse biasing

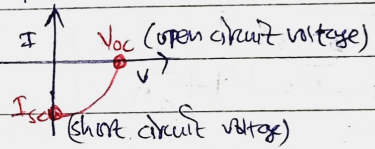
$$V_{net} = V_{ext} + V_{barrier}$$

zener diode \rightarrow Reverse bias

LED - forward bias

Photodiode - Reverse bias

Solar cell -



* Transistor

Forward bias

Reverse bias

I_C = collector current
 I_B = base current

Logic gates

(1) OR gate $Y = A + B$



(2) AND gate $Y = A \cdot B$



(3) NOT gate $Y = \bar{A}$



(4) NOR gate (OR + NOT)



(5) NAND (NOT + AND)



$$\overline{A+B} = \bar{A} \cdot \bar{B} \quad \overline{A \cdot B} = \bar{A} + \bar{B}$$

$$A \cdot B = \overline{\bar{A} \cdot \bar{B}} \quad \bar{A} \cdot \bar{B} = \overline{A + B}$$

$$\overline{A+B} = A + B \quad \overline{\bar{A} + \bar{B}} = A \cdot B$$